

Sample &

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TLV713P-Q1

TLV713P-Q1 Capacitor-Free, 150-mA, Low-Dropout Regulator With Foldback Current Limit for Portable Devices

Technical

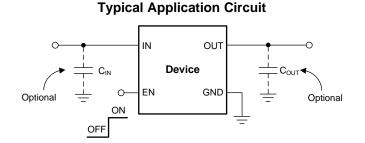
Documents

Features 1

- AEC-Q100 Qualified with the Following Results:
 - Device Temperature Grade 1: –40°C to 125°C Ambient Operating Temperature Range
 - Device HBM ESD Classification Level H2
 - Device CDM ESD Classification Level C4B
- Input Voltage Range: 1.4 V to 5.5 V
- Stable Operation With or Without Capacitors
- Foldback Overcurrent Protection
- Package: 5-Pin SOT-23
- Very Low Dropout: 230 mV at 150 mA
- Accuracy: 1%
- Low Io: 50 µA
- Available in Fixed-Output Voltages:
 - 1 V to 3.3 V
- High PSRR: 65 dB at 1 kHz
- Active Output Discharge

Applications 2

- Automotive Head Units
- Audio Amplifiers
- **DI Clusters**
- ADAS ECUs
- Microprocessor Rails
- USBs
- **Body Electronics**



3 Description

Tools &

Software

The TLV713P-Q1 series of low-dropout (LDO) linear regulators are low quiescent current LDOs with excellent line and load transient performance and are designed for power-sensitive applications. These devices provide a typical accuracy of 1%.

Support &

Community

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The TLV713P-Q1 series of devices is designed to be stable without an output capacitor. The removal of the output capacitor allows for a very small solution size. However, the TLV713P-Q1 series is also stable with any output capacitor if an output capacitor is used.

The TLV713P-Q1 also provides inrush current control during device power-up and enabling. The TLV713P-Q1 limits the input current to the defined current limit to avoid large currents from flowing from the input power source. This functionality is especially important in battery-operated devices.

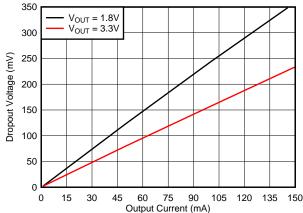
The TLV713P-Q1 series is available in a standard DBV package and provides an active pulldown circuit to quickly discharge output loads. The TLV713P-Q1 is suited for automotive applications because the device is qualified for AEC-Q100 grade 1.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)	
TLV713P-Q1	SOT-23 (5)	2.90 mm × 1.60 mm	

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Dropout Voltage vs Output Current





SBVS266-MAY 2015

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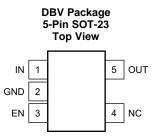
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4 Revision History

DATE	REVISION	NOTES	
May 2015	*	Initial release.	



5 Pin Configurations and Functions



Pin Functions

1	PIN I/O		
NAME			DESCRIPTION
NAME	SOT-23		
EN	3	I	Enable pin. Driving EN over 0.9 V turns on the regulator. Driving EN below 0.4 V puts the regulator into shutdown mode.
GND	2	—	Ground pin
IN	1	I	Input pin. A small capacitor is recommended from this pin to ground. See the <i>Input and Output Capacitor Considerations</i> section in the <i>Feature Description</i> for more details.
NC	4	_	No internal connection
OUT	5	0	Regulated output voltage pin. For best transient response, a small $1-\mu$ F ceramic capacitor is recommended from this pin to ground. See the <i>Input and Output Capacitor Considerations</i> section in the <i>Feature Description</i> for more details.
Thermal pad —		—	The thermal pad is electrically connected to the GND node. Connect to the GND plane for improved thermal performance.

6 Specifications

6.1 Absolute Maximum Ratings

Over operating junction temperature range ($T_{J} = 25^{\circ}$ C), unless otherwise noted. All voltages are with respect to GND.⁽¹⁾

		MIN	MAX	UNIT	
	Input, V _{IN}	-0.3	6	V	
Voltage	Enable, V _{EN}	-0.3	V _{IN} + 0.3	V	
	Output, V _{OUT}	-0.3	3.6	V	
Current	Maximum output, I _{OUT(max)}		Internally limited		
Output short-circuit duration			Indefinite		
Total power dissipation	Continuous, P _{D(tot)}	See	See the Thermal Information		
Tama analuna	Storage, T _{stg}	-55	150	°C	
Temperature	Junction, T _J	-55	125	°C	

(1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatia discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	N/
V _(ESD)	Electrostatic discharge	Charged device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±500	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted).

		MIN	NOM	MAX	UNIT
V _{IN}	Input voltage	1.4		5.5	V
V _{EN}	Enable range	0		V _{IN}	V
I _{OUT}	Output current	0		150	mA
C _{IN}	Input capacitor	0	1		μF
C _{OUT}	Output capacitor	0	0.1	100	μF
TJ	Operating junction temperature range	-40		125	°C

6.4 Thermal Information

		TLV713P-Q1	
	THERMAL METRIC	DBV (SOT-23)	UNIT
		5 PINS	
$R_{ extsf{ heta}JA}$	Junction-to-ambient thermal resistance	249	°C/W
R _{0JC(top)}	Junction-to-case (top) thermal resistance	172.7	°C/W
$R_{ heta JB}$	Junction-to-board thermal resistance	76.7	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	49.7	°C/W
Ψ _{JB}	Junction-to-board characterization parameter	75.8	°C/W
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	n/a	°C/W

6.5 Electrical Characteristics

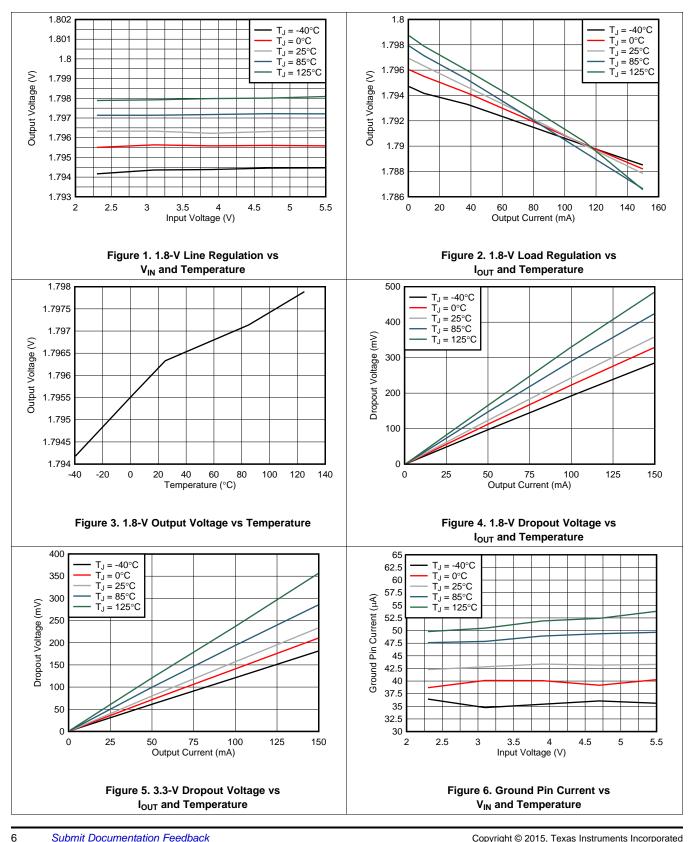
Over operating temperature range (T_J, T_A = -40° C to 125°C), V_{IN(nom)} = V_{OUT(nom)} + 0.5 V or V_{IN(nom)} = 2 V (whichever is greater), I_{OUT} = 1 mA, V_{EN} = V_{IN}, and C_{OUT} = 0.47 μ F, unless otherwise noted. Typical values are at T_J = 25°C.

PA	RAMETER	TEST CONDITIONS		MIN	TYP	MAX	UNIT	
V _{IN}	Input voltage range			1.4		5.5	V	
V _{OUT}	Output voltage range			1		3.3	V	
		$V_{OUT} \ge 1.8 \text{ V}; \text{ T}_{\text{J}}, \text{ T}_{\text{A}} = 25^{\circ}$	C	-1%		1%		
	DC output accuracy	$V_{OUT} < 1.8 V; T_J, T_A = 25^{\circ}$	°C	-20		20	mV	
		$V_{OUT} \ge 1.2 \text{ V}; -40^{\circ}\text{C} \le \text{T}_{\text{J}},$	T _A ≤ 125°C	-1.5%		1.5%		
		$V_{OUT} < 1.2 \text{ V}; -40^{\circ}\text{C} \le \text{T}_{\text{J}},$	$/_{OUT} < 1.2 \text{ V}; -40^{\circ}\text{C} \le \text{T}_{\text{J}}, \text{T}_{\text{A}} \le 125^{\circ}\text{C}$			50	mV	
$\Delta V_{OUT(\Delta VIN)}$	Line regulation	Max [V _{OUT(nom)} + 0.5 V, V	$_{\rm N} = 2.0 \text{ V}] \le V_{\rm IN} \le 5.5 \text{ V}$		1	5	mV	
$\Delta V_{OUT(\Delta IOUT)}$	Load regulation	$0 \text{ mA} \le I_{OUT} \le 150 \text{ mA}$			10	30	mV	
			1 V \leq V _{OUT} $<$ 1.8 V, I _{OUT} $=$ 150 mA		600	900	mV	
			$1.8 \text{ V} \le \text{V}_{\text{OUT}} < 2.1 \text{ V}, \text{ I}_{\text{OUT}} = 30 \text{ mA}$		70		mV	
			$1.8 \text{ V} \le \text{V}_{\text{OUT}} < 2.1 \text{ V}, \text{ I}_{\text{OUT}} = 150 \text{ mA}$		350	575	mV	
		$V_{OUT} = 0.98 \times V_{OUT(nom)};$ T _{.1} , T _A = -40°C to 85°C	$2.5 \text{ V} \leq \text{V}_{\text{OUT}} < 3 \text{ V}, \text{ I}_{\text{OUT}} = 30 \text{ mA}$		50		mV	
		1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1, 1	$2.5 \text{ V} \le \text{V}_{\text{OUT}} < 3 \text{ V}, \text{ I}_{\text{OUT}} = 150 \text{ mA}$		246	445	mV	
V _{DO} Dropo	Dropout voltage		$3 \text{ V} \leq \text{V}_{\text{OUT}} < 3.6 \text{ V}, \text{ I}_{\text{OUT}} = 30 \text{ mA}$		46		mV	
			$3 \text{ V} \leq \text{V}_{\text{OUT}} < 3.6 \text{ V}, \text{ I}_{\text{OUT}} = 150 \text{ mA}$		230	420	mV	
		$V_{OUT} = 0.98 \times V_{OUT(nom)};$ T _J , T _A = -40°C to 125°C	$1 \text{ V} \le \text{V}_{\text{OUT}} < 1.8 \text{ V}, \text{ I}_{\text{OUT}} = 150 \text{ mA}$		600	1020	mV	
			1.8 V ≤ V _{OUT} < 2.1 V, I _{OUT} = 150 mA		350	695	mV	
			2.5 V ≤ V _{OUT} < 3 V, I _{OUT} = 150 mA		246	600	mV	
			$3 \text{ V} \leq \text{V}_{\text{OUT}} < 3.6 \text{ V}, \text{ I}_{\text{OUT}} = 150 \text{ mA}$		230	560	mV	
GND	Ground pin current	I _{OUT} = 0 mA			50	75	μA	
SHUTDOWN	Shutdown current	$V_{EN} \le 0.4 \text{ V}; 2.0 \text{ V} \le V_{IN} \le$	5.5 V; T _J , T _A = 25°C		0.1	1	μA	
		V _{IN} = 3.3 V,	f = 100 Hz		70		dB	
PSRR	Power-supply rejection ratio	Power-supply	$V_{IN} = 3.3 V,$ $V_{OUT} = 2.8 V,$	f = 10 kHz		55		dB
		$I_{OUT} = 30 \text{ mA}$	f = 1 MHz		55		dB	
V _n	Output noise voltage	BW = 100 Hz to 100 kHz,	V _{IN} = 2.3 V, V _{OUT} = 1.8 V, I _{OUT} = 10 mA		73		μV_{RMS}	
STR	Start-up time	C _{OUT} = 1.0 μF, I _{OUT} = 150	mA		100		μs	
V _{HI}	Enable high (enabled)			0.9		V _{IN}	V	
V _{LO}	Enable low (disabled)			0		0.4	V	
EN	EN pin current	EN = 5.5 V			0.01		μA	
R _{PULLDOWN}	Pulldown resistor	V _{IN} = 4 V			120		Ω	
		$V_{IN} = 3.8 \text{ V}, V_{OUT} = 3.3 \text{ V}$		175			mA	
		$V_{IN} = 3.0 \text{ V}, V_{OUT} = 2.5 \text{ V}$		175			mA	
LIM	Output current limit	V _{IN} = 2.3 V, V _{OUT} = 1.8 V		175			mA	
		V _{IN} = 2.0 V, V _{OUT} = 1.2 V		175			mA	
		V _{IN} = 2.0 V, V _{OUT} = 1.0 V		175			mA	
sc	Short-circuit current	V _{OUT} = 0 V			40		mA	
T	The second states to	Shutdown, temperature in	creasing		158		°C	
T _{SD}	Thermal shutdown	Reset, temperature decre	asing		140		°C	



6.6 Typical Characteristics

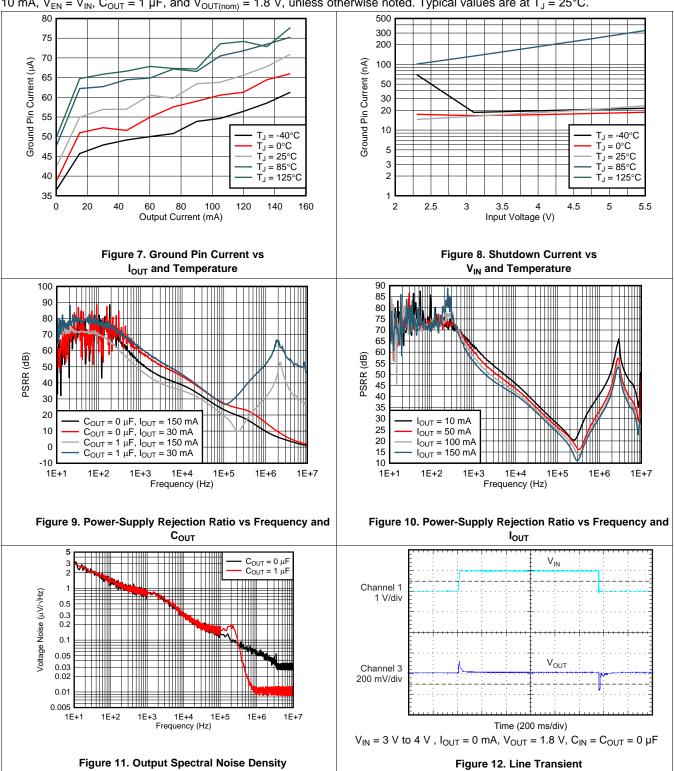
Over operating temperature range ($T_J = -40^{\circ}C$ to 125°C), $V_{IN} = V_{OUT(nom)} + 0.5$ V or 2.0 V (whichever is greater), $I_{OUT} = 10$ mA, $V_{EN} = V_{IN}$, $C_{OUT} = 1$ µF, and $V_{OUT(nom)} = 1.8$ V, unless otherwise noted. Typical values are at $T_J = 25^{\circ}C$.



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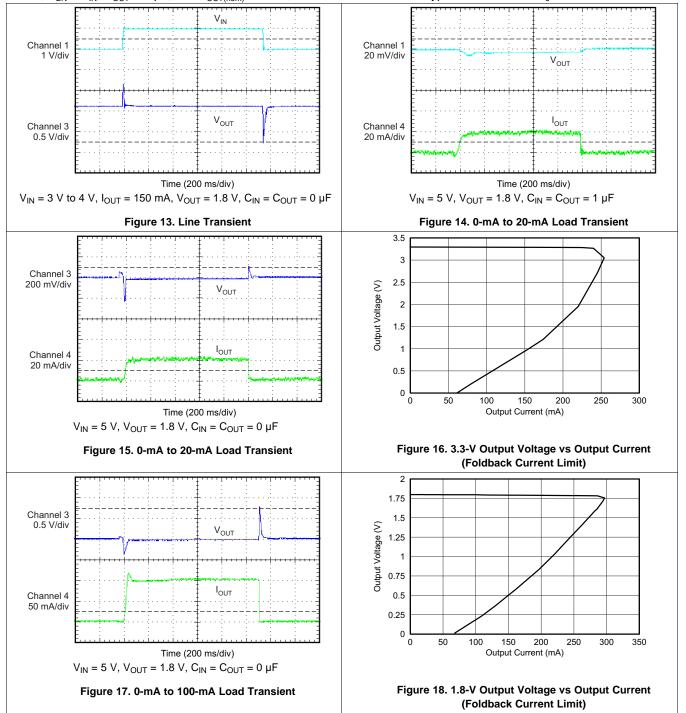
Typical Characteristics (continued)



Over operating temperature range ($T_J = -40^{\circ}$ C to 125°C), $V_{IN} = V_{OUT(nom)} + 0.5$ V or 2.0 V (whichever is greater), $I_{OUT} = 10$ mA, $V_{EN} = V_{IN}$, $C_{OUT} = 1$ µF, and $V_{OUT(nom)} = 1.8$ V, unless otherwise noted. Typical values are at $T_J = 25^{\circ}$ C.



Over operating temperature range ($T_J = -40^{\circ}$ C to 125°C), $V_{IN} = V_{OUT(nom)} + 0.5$ V or 2.0 V (whichever is greater), $I_{OUT} = 10$ mA, $V_{EN} = V_{IN}$, $C_{OUT} = 1$ µF, and $V_{OUT(nom)} = 1.8$ V, unless otherwise noted. Typical values are at $T_J = 25^{\circ}$ C.

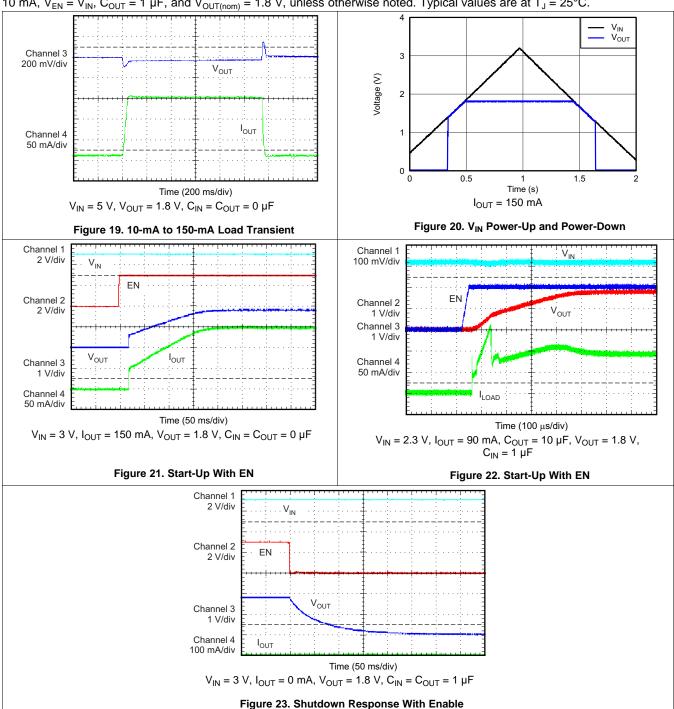




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Typical Characteristics (continued)



Over operating temperature range ($T_J = -40^{\circ}$ C to 125°C), $V_{IN} = V_{OUT(nom)} + 0.5$ V or 2.0 V (whichever is greater), $I_{OUT} = 10$ mA, $V_{EN} = V_{IN}$, $C_{OUT} = 1 \mu$ F, and $V_{OUT(nom)} = 1.8$ V, unless otherwise noted. Typical values are at $T_J = 25^{\circ}$ C.

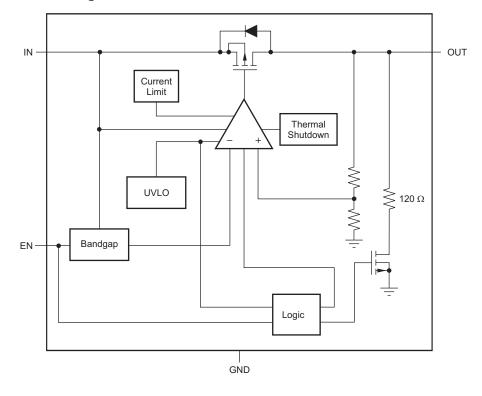
7 Detailed Description

7.1 Overview

These devices belong to a family of low-dropout (LDO) regulators that consume low quiescent current and deliver excellent line and load transient performance. These characteristics, combined with low noise and very good PSRR with little ($V_{IN} - V_{OUT}$) headroom, make this family of devices ideal for RF portable applications.

This family of regulators offers current limit and thermal protection. Device operating junction temperature is –40°C to 125°C.

7.2 Functional Block Diagram





7.3 Feature Description

7.3.1 Undervoltage Lockout (UVLO)

The TLV713P-Q1 uses a UVLO circuit that disables the output until the input voltage is greater than the rising UVLO voltage. This circuit ensures that the device does not exhibit any unpredictable behavior when the supply voltage is lower than the operational range of the internal circuitry, $V_{IN(min)}$. During UVLO disable, the output of the TLV713P-Q1 is connected to ground with a 120- Ω pulldown resistor.

7.3.2 Shutdown

The enable pin (EN) is active high. Enable the device by forcing the EN pin to exceed $V_{EN(high)}$ (0.9 V, minimum). Turn off the device by forcing the EN pin to drop below 0.4 V. If shutdown capability is not required, connect EN to IN.

The TLV713P-Q1 has an internal pulldown MOSFET that connects a 120- Ω resistor to ground when the device is disabled. The discharge time after disabling depends on the output capacitance (C_{OUT}) and the load resistance (R_L) in parallel with the 120- Ω pulldown resistor. The time constant is calculated in Equation 1.

7.3.3 Foldback Current Limit

 $\tau = \frac{120 \cdot R_{L}}{120 \cdot R_{L}} \cdot C_{OUT}$

The TLV713P-Q1 has an internal foldback current limit that helps protect the regulator during fault conditions. The current supplied by the device is gradually reduced when the output voltage decreases. When the output is shorted, the LDO supplies a typical current of 40 mA. Output voltage is not regulated when the device is in current limit, and is calculated by Equation 2:

 $V_{OUT} = I_{LIMIT} \times R_{LOAD}$

The PMOS pass transistor dissipates $[(V_{IN} - V_{OUT}) \times I_{LIMIT}]$ until thermal shutdown is triggered and the device turns off. The device is turned on by the internal thermal shutdown circuit during cool down. If the fault condition continues, the device cycles between current limit and thermal shutdown. See the *Thermal Information* section for more details.

The TLV713P-Q1 PMOS pass element has a built-in body diode that conducts current when the voltage at OUT exceeds the voltage at IN. This current is not limited, so if extended reverse voltage operation is anticipated, external limiting to 5% of the rated output current is recommended.

7.3.4 Thermal Protection

Thermal protection disables the output when the junction temperature rises to approximately 158°C, allowing the device to cool. When the junction temperature cools to approximately 140°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit may cycle on and off. This cycling limits regulator dissipation, protecting the device from damage as a result of overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heatsink. For reliable operation, junction temperature must be limited to 125°C maximum. To estimate the margin of safety in a complete design (including heatsink), increase the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions.

The TLV713P-Q1 internal protection circuitry is designed to protect against overload conditions. This circuitry is not intended to replace proper heatsinking. Continuously running the TLV713P-Q1 into thermal shutdown degrades device reliability.

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(2)

(1)

7.4 Device Functional Modes

7.4.1 Normal Operation

The device regulates to the nominal output voltage under the following conditions:

- The input voltage is at least as high as V_{IN(min)}.
- The input voltage is greater than the nominal output voltage added to the dropout voltage.
- The enable voltage has previously exceeded the enable rising threshold voltage and has not decreased below the enable falling threshold.
- The output current is less than the current limit.
- The device junction temperature is less than the maximum specified junction temperature.

7.4.2 Dropout Operation

If the input voltage is lower than the nominal output voltage plus the specified dropout voltage, but all other conditions are met for normal operation, the device operates in dropout mode. In this mode of operation, the output voltage is the same as the input voltage minus the dropout voltage. The transient performance of the device is significantly degraded because the pass device is in the linear region and no longer controls the current through the LDO. Line or load transients in dropout can result in large output voltage deviations.

7.4.3 Disabled

The device is disabled under the following conditions:

- The enable voltage is less than the enable falling threshold voltage or has not yet exceeded the enable rising threshold.
- The device junction temperature is greater than the thermal shutdown temperature.

Table 1 shows the conditions that lead to the different modes of operation.

OPERATING MODE	PARAMETER					
OPERATING MODE	V _{IN}	V _{EN}	Ι _{ουτ}	TJ		
Normal mode	$V_{IN} > V_{OUT(nom)} + V_{DO}$ and $V_{IN} > V_{IN(min)}$	$V_{EN} > V_{EN(high)}$	I _{OUT} < I _{LIM}	T _J < 125°C		
Dropout mode	$V_{IN(min)} < V_{IN} < V_{OUT(nom)} + V_{DO}$	$V_{EN} > V_{EN(high)}$	—	T _J < 125°C		
Disabled mode (any true condition disables the device)	_	V _{EN} < V _{EN(low)}	_	T _J > 158°C		

Table 1. Device Functional Mode Comparison



8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Input and Output Capacitor Considerations

The TLV713P-Q1 uses an advanced internal control loop to obtain stable operation both with and without the use of input or output capacitors. The TLV713P-Q1 dynamic performance is improved with the use of an output capacitor. An output capacitance of 0.1 μ F or larger generally provides good dynamic response. X5R- and X7R-type ceramic capacitors are recommended because these capacitors have minimal variation in value and equivalent series resistance (ESR) over temperature.

Although an input capacitor is not required for stability, good analog design practice is to connect a $0.1-\mu$ F to $1-\mu$ F capacitor from IN to GND. This capacitor counteracts reactive input sources and improves transient response, input ripple, and PSRR. An input capacitor is recommended if the source impedance is more than 0.5Ω . A higher-value capacitor may be necessary if large, fast, rise-time load transients are anticipated or if the device is located several inches from the input power source.

8.1.2 Dropout Voltage

The TLV713P-Q1 uses a PMOS pass transistor to achieve low dropout. When $(V_{IN} - V_{OUT})$ is less than the dropout voltage (V_{DO}) , the PMOS pass device is in the linear region of operation and the input-to-output resistance is the $R_{DS(on)}$ of the PMOS pass element. V_{DO} scales approximately with output current because the PMOS device behaves like a resistor in dropout. As with any linear regulator, PSRR and transient response are degraded when $(V_{IN} - V_{OUT})$ approaches dropout.

8.1.3 Transient Response

As with any regulator, increasing the size of the output capacitor reduces over- and undershoot magnitude but increases the duration of the transient response.

8.2 Typical Application

Several versions of the TPS713P-Q1 are ideal for powering the MSP430 microcontroller.

Figure 24 shows a diagram of the TLV713P-Q1 powering an MSP430 microcontroller. Table 2 shows potential applications of some voltage versions.

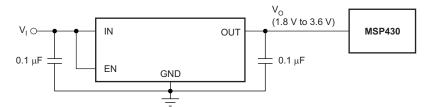


Figure 24. TLV713P-Q1 Powering a Microcontroller

Table 2.	Typical	MSP430	Applications
----------	---------	---------------	--------------

DEVICE	V _{о∪т} (Тур)	APPLICATION
TLV71318P-Q1	1.8 V	Allows for lowest power consumption with many MSP430s
TLV71325P-Q1	2.5 V	2.2-V supply required by many MSP430s for flash programming and erasing

8.2.1 Design Requirements

Table 3 lists the design requirements.

Table 3. Design Parameters

PARAMETER	DESIGN REQUIREMENT
Input voltage	4.2 V to 3 V (Lithium Ion battery)
Output voltage	1.8 V, ±1%
DC output current	10 mA
Peak output current	75 mA
Maximum ambient temperature	65°C

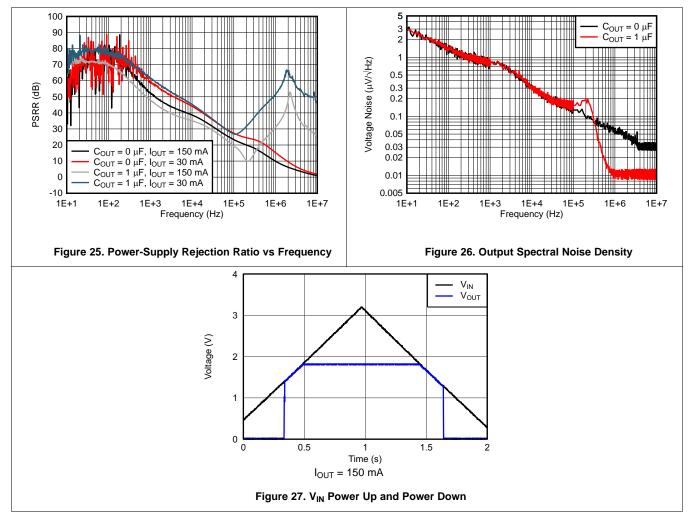
8.2.2 Detailed Design Procedure

An input capacitor is not required for this design because of the low impedance connection directly to the battery.

No output capacitor allows for the minimal possible inrush current during start-up, ensuring the 180-mA maximum input current limit is not exceeded.



8.2.3 Application Curves



8.3 Do's and Don'ts

For best transient performance, place at least one 0.1-µF ceramic capacitor as close as possible to the OUT pin of the regulator and at least one 1-uF capacitor as close as possible to the IN pin of the regulator.

Do not place the output capacitor more than 10 mm away from the regulator.

Do not exceed the absolute maximum ratings.

Do not continuously operate the device in current limit or near thermal shutdown.



9 Power-Supply Recommendations

These devices are designed to operate from an input voltage supply range from 1.4 V to 5.5 V. The input voltage range must provide adequate headroom for the device to have a regulated output. This input supply must be well-regulated and stable. If the input supply is noisy, additional input capacitors with low ESR can help improve the output noise performance.

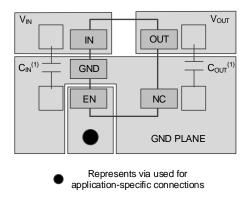
10 Layout

10.1 Layout Guidelines

10.1.1 Board Layout Recommendations to Improve PSRR and Noise Performance

Input and output capacitors must be placed as close to the device pins as possible. To improve ac performance (such as PSRR, output noise, and transient response), TI recommends that the board be designed with separate ground planes for V_{IN} and V_{OUT} , with the ground plane connected only at the device GND pin. In addition, the output capacitor ground connection must be connected directly to the device GND pin. High-ESR capacitors may degrade PSRR performance.

10.2 Layout Example



(1) Not required.





10.3 Power Dissipation

The ability to remove heat from the die is different for each package type, presenting different considerations in the printed-circuit-board (PCB) layout. The PCB area around the device that is free of other components moves the heat from the device to the ambient air. Performance data for JEDEC low- and high-K boards are given in the table. Using heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers also improves the heatsink effectiveness.

Power dissipation depends on input voltage and load conditions. Power dissipation (P_D) can be approximated by the product of the output current times the voltage drop across the output pass element (V_{IN} to V_{OUT}), as shown in Equation 3.

$$P_{D} = (V_{IN} - V_{OUT}) \times I_{OUT}$$

(3)

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Estimating the junction temperature can be done by using the thermal metrics Ψ_{JT} and Ψ_{JB} , as discussed in the table. These metrics are a more accurate representation of the heat transfer characteristics of the die and the package than R_{BJA}. The junction temperature can be estimated with Equation 4.

 $\Psi_{JT}: T_{J} = T_{T} + \Psi_{JT} \bullet P_{D}$

 Ψ_{JB} : $T_J = T_B + \Psi_{JB} \bullet P_D$

where

- P_D is the power dissipation shown by Equation 3,
- T_T is the temperature at the center-top of the device package,
- T_B is the PCB temperature measured 1 mm away from the device package on the PCB surface.

(4)

NOTE

Both T_T and T_B can be measured on actual application boards using a thermo-gun (an infrared thermometer).

For more information about measuring T_T and T_B , see application note Using New Thermal Metrics (SBVA025), available for download at www.ti.com.



11 Device and Documentation Support

11.1 Device Support

11.1.1 Development Support

11.1.1.1 Evaluation Modules

Three evaluation modules (EVMs) are available to assist in the initial circuit performance evaluation using the TLV713P-Q1:

- TLV71312PEVM-171
- TLV71318PEVM-171
- TLV71333PEVM-171

These EVMs come populated with the commercial version of the device in the DQN package; however, they can be used for parametric evaluation. These EVMs can be requested at the Texas Instruments website through the device product folders or purchased directly from the TI eStore.

11.1.1.2 Spice Models

Computer simulation of circuit performance using SPICE is often useful when analyzing the performance of analog circuits and systems. A SPICE model for the TLV713P-Q1 is available through the product folders under *Tools & Software*.

11.1.2 Device Nomenclature

Table 4. Ordering Information^{(1) (2)}

PRODUCT	V _{OUT}
TLV713P xxPQyyyz Q1	 xx is the nominal output voltage. For output voltages with a resolution of 100 mV, two digits are used in the ordering number (for example, 28 = 2.8 V). P is optional; devices with P have an LDO regulator with an active output discharge. yyy is the package designator. z is the package quantity. R is for reel (3000 pieces), T is for tape (250 pieces).

(1) For the most current package and ordering information see the Package Option Addendum at the end of this document, or visit the device product folder on www.ti.com.

(2) Output voltages from 1.0 V to 3.3 V in 50-mV increments are available. Contact the factory for details and availability.

11.2 Documentation Support

11.2.1 Related Documentation

- Using New Thermal Metrics, SBVA025
- TLV713xxEVM-171 User's Guide, SLVU771

11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E[™] Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration

among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support TI's Design Support Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.4 Trademarks

E2E is a trademark of Texas Instruments. All other trademarks are the property of their respective owners.



11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



11-Jun-2015

PACKAGING INFORMATION

Orderable Device	Status	Package Type	•	Pins	•		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
TLV71310PQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	ZBGW	Samples
TLV71312PQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	ZBHW	Samples
TLV71318PQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	ZBIW	Samples
TLV71325PQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	ZBJW	Samples
TLV71333PQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	ZBKW	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

11-Jun-2015

⁽⁶⁾ Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TLV713P-Q1 :

Catalog: TLV713P

NOTE: Qualified Version Definitions:

• Catalog - TI's standard catalog product

PACKAGE MATERIALS INFORMATION

www.ti.com

Texas Instruments

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV71310PQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV71312PQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV71318PQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV71325PQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV71333PQDBVRQ1	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3

TEXAS INSTRUMENTS

www.ti.com

PACKAGE MATERIALS INFORMATION

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV71310PQDBVRQ1	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV71312PQDBVRQ1	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV71318PQDBVRQ1	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV71325PQDBVRQ1	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV71333PQDBVRQ1	SOT-23	DBV	5	3000	180.0	180.0	18.0

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



- All linear dimensions are in millimeters. A.
 - This drawing is subject to change without notice. Β.
 - Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side. C.
 - D. Falls within JEDEC MO-178 Variation AA.



DBV (R-PDSO-G5)

PLASTIC SMALL OUTLINE



NOTES:

A. All linear dimensions are in millimeters.B. This drawing is subject to change without notice.

- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.



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